

## ■ Features

- High Output Power:  $P_{\text{sat}}=48.0\text{dBm}$  (Typ.)
- High Gain:  $G_p=11.0\text{dB}$  (Typ.)
- High Power Added Efficiency:  $\text{PAE}=40\%$  (Typ.)
- Broad Band: 8.5 to 9.8GHz
- Impedance Matched  $Z_{\text{in}}/Z_{\text{out}} = 50\text{ohm}$
- Hermetically Sealed Package

## ■ Description

The SGC8598-50A-R is a high power GaN-HEMT that is internally matched for X-band radar bands to provide optimum power and gain in a 50ohm system.



### ABSOLUTE MAXIMUM RATING (Case Temperature $T_c=25\text{ deg.C}$ )

Item	Symbol	Rating	Unit
Drain-Source Voltage	$V_{\text{DS}}$	55	V
Gate-Source Voltage	$V_{\text{GS}}$	-15	V
Storage Temperature	$T_{\text{stg}}$	-55 to +125	deg.C
Channel Temperature	$T_{\text{ch}}$	+250	deg.C

### RECOMMENDED OPERATING CONDITION

Item	Symbol	Condition	Limit	Unit
Drain-Source Voltage	$V_{\text{DS}}$		$\leq 50$	V
Forward Gate Current	$I_{\text{GF}}$	$R_g=100\text{ohm}$	$\leq 4$	mA
Reverse Gate Current	$I_{\text{GR}}$	$R_g=100\text{ohm}$	$\geq -2.2$	mA
Channel Temperature	$T_{\text{ch}}$		$< +200$	deg.C

### ELECTRICAL CHARACTERISTICS (Case Temperature $T_c=25\text{ deg.C}$ )

Item	Symbol	Condition	Limit			Unit
			Min.	Typ.	Max.	
Pinch-off Voltage	$V_p$	$V_{\text{DS}}=50\text{V}, I_{\text{DS}}=3\text{mA}$	-	-4.5	-	V
Frequency Range	Freq.	$V_{\text{DS}}=50\text{V-typ.}$ $I_{\text{DS(DC)}}=0.17\text{A-typ.}$ Pulse Width=100μsec. Duty=10%	8.5	-	9.8	GHz
Output Power at $\text{Pin}=38\text{dBm}$	$P_{\text{sat}}$		47.0	48.0	-	dBm
Power Gain at $\text{Pout}=47\text{dBm}$	$G_p$		10.0	11.0	-	dB
Drain Current at $\text{Pin}=38\text{dBm}$	$I_{\text{DSR}}$		-	2.8	4.1	A
Power Added Efficiency at $\text{Pin}=38\text{dBm}$	PAE		-	40	-	%
Gain Flatness	$\Delta G$		-	1.6	-	dB
Thermal Resistance	$R_{\text{th}}$	Channel to Case ( $P_{\text{diss}}=50\text{W}, \text{CW}$ )	-	2.4	3.0	deg.C/W

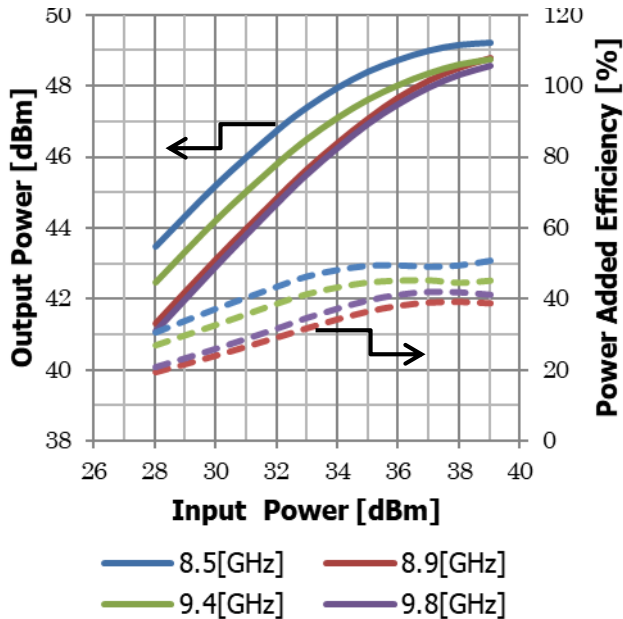
CASE STYLE	IK		
RoHS Compliance	YES		
ESD	Class 2	2000V to <4000V	

Note: Based on ANSI/ESDA/JEDEC JS-001-2012( $C=100\text{pF}$ ,  $R=1.5\text{kohm}$ )

## ● RF Characteristics

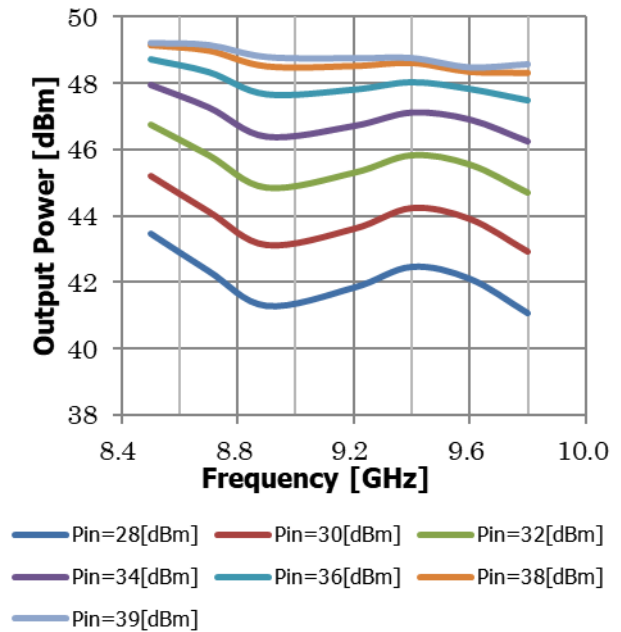
### Output Power & Power Added Efficiency vs. Input Power

$V_{DS}=50V$ ,  $I_{DS(DC)}=0.17A$   
 $PW=100\mu sec.$ , Duty=10%



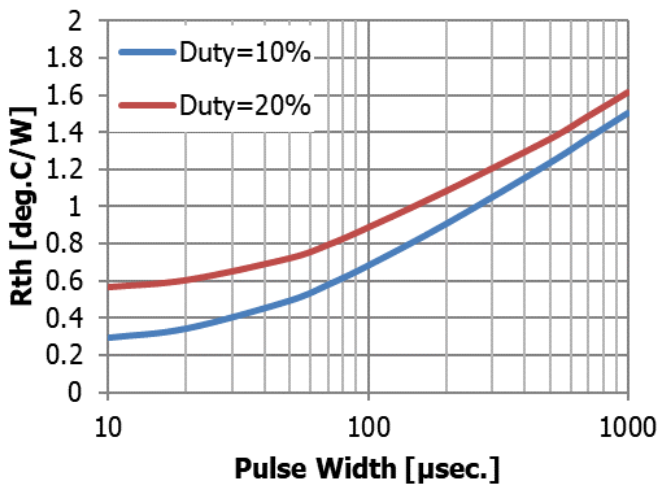
### Output Power vs. Frequency

$V_{DS}=50V$ ,  $I_{DS(DC)}=0.17A$   
 $PW=100\mu sec.$ , Duty=10%

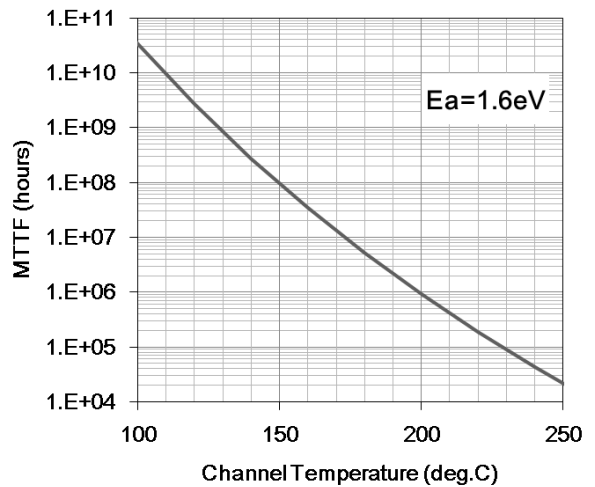


## ● Thermal Characteristics In Pulsed Operation

### Rth vs. Pulse Width $T_c=75deg.C$



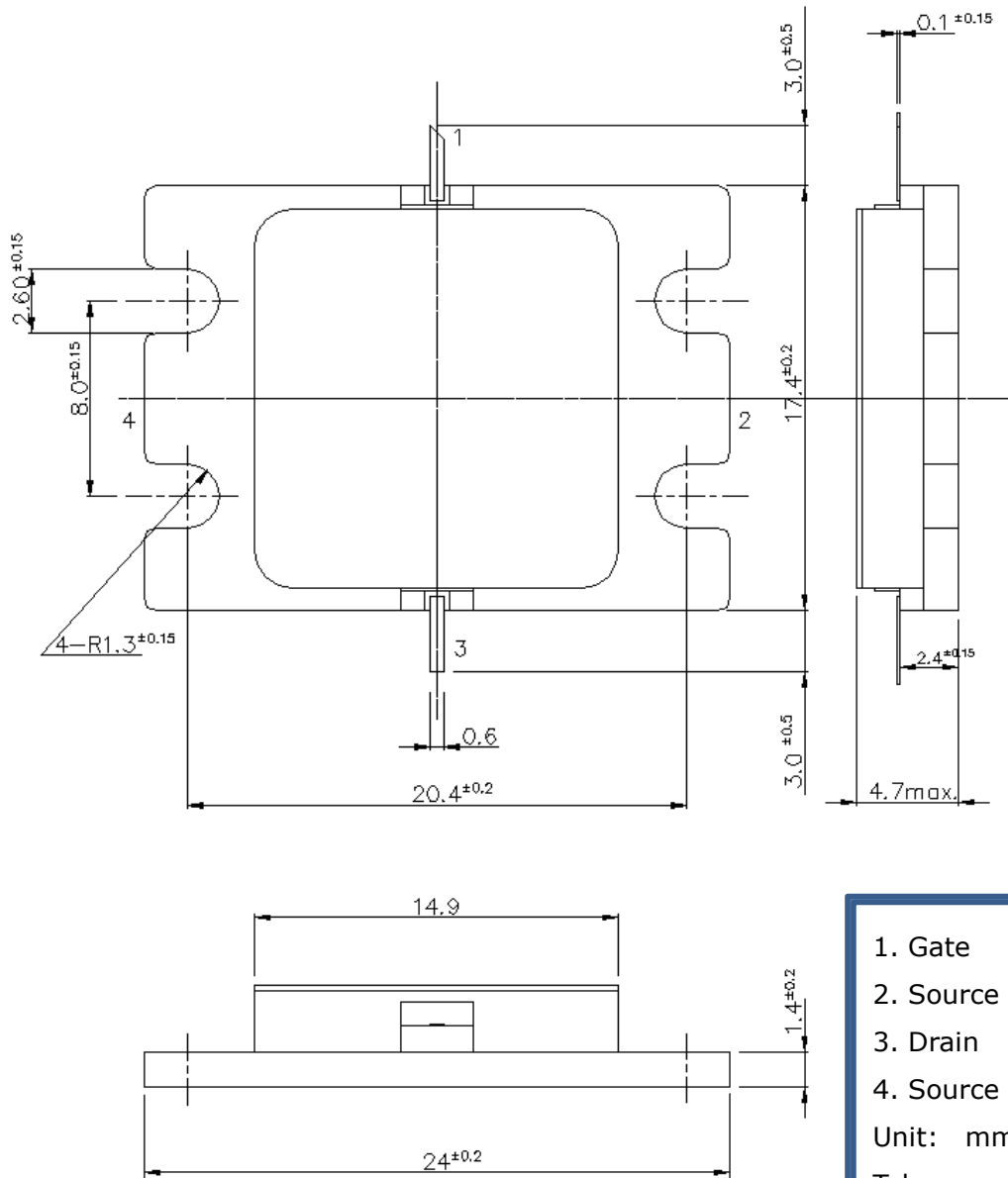
### MTTF vs. Tch





● **Package Outline**

**Case Style : IK**



1. Gate  
2. Source  
3. Drain  
4. Source  
Unit: mm  
Tolerance:  $\pm$  0.15

## **For Safety, Observe the Following Procedures Environmental Management**

- Do not put this product into the mouth.
- Do not alter the form of this product into a gas, powder, or liquid through burning, crushing, or chemical processing as these by-products are dangerous to the human body if inhaled, ingested, or swallowed.
- Respect all applicable laws of the country when discarding this product.  
This product must be disposed in accordance with methods specified by applicable hazardous waste procedures.

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